

CT Micro

Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Temperature range 55 °C to 100 °C

Applications

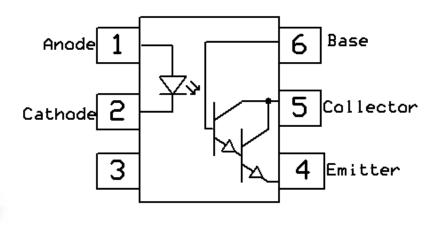
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Description

The 4N2X, 4N3X, H11BX and TIL113 series consists of a photo darlington optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package with bending options.

Package Outline

Schematic



Note: Different bending options available. See package dimension.



Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V _{RMS}	
Topr	Operating temperature	-55 ~ +100	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
TsoL	Soldering temperature	260	°C	
Emitter		·	<u> </u>	
l _F	Forward current	60	mA	
I _F (TRANS)	Peak transient current (≤1µs P.W,300pps)	1	А	
V _R	Reverse voltage	6	V	
PD	Power dissipation	100	mW	
Detector		·	<u> </u>	
PD	Power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	55	V	
Вусво	Collector-Base Breakdown Voltage	55	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	7	V	
B _{VEBO}	Emitter-Base Breakdown Voltage	7	V	



Electrical Characteristics $T_A = 25$ °C (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =10mA		1.2	1.7	V	
I _R	Reverse Current	V _R = 6V	-	-	5	μΑ	
Cin	Input Capacitance	f= 1MHz	-	45	-	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B _{VCEO}	B _{VCEO} Collector-Emitter Breakdown I _C = 100μA		55	-	-	V	
Bveco	Emitter-Collector Breakdown	I _E = 1mA	7	-	-	V	
Вусво	Collector-Base Breakdown	I _C = 100μA	55	-	-	V	
ICEO	Collector-Emitter Dark Current	V _{CE} = 10V, I _F =0mA	-	-	50	nA	

Transfer Characteristics

Symbol	P	arameters	Test Conditions	Min	Тур	Max	Units	Notes
		4N29, 4N30		100	-	-		
		4N31	I _F = 10mA, V _{CE} = 10V	50	-	-		
	0	4N32, 4N33		500	-	-		
CTD	Current	H11B1		500	-	-	0/	
CTR	Transfer	H11B2	I _F = 1mA, V _{CE} = 10V	200	-	-	%	
	Ratio	H11B3]	100	-	-		
		H11B255	I _F = 10mA, V _{CE} = 5V	100	-	-		
		TIL113	I _F = 10mA, V _{CE} = 1V	300	-	-		
	Collector- Emitter	4N29, 4N30, 4N32, 4N33	I _F = 8mA, I _C = 2mA	-	-	1.0		
.,	Saturation	4N31, TIL113	I _F = 8mA, I _C = 2mA	-	-	1.2	.,	
VCE(SAT)	V _{CE(SAT)} Voltage	H11B1, H11B2, H11B3	I _F = 1mA, I _C = 1mA	-	-	1.0	V	
		H11B255	I _F =50mA, I _C = 50mA	-	-	1.0		
Rio	Isolation Resistance		V _{IO} = 500V _{DC}	1x10 ¹¹			Ω	
C _{IO}	Isolation Capacitance		f= 1Mhz		0.25		pF	

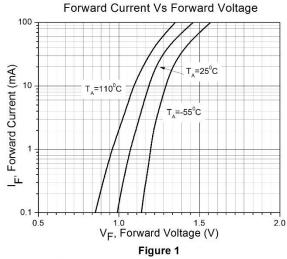


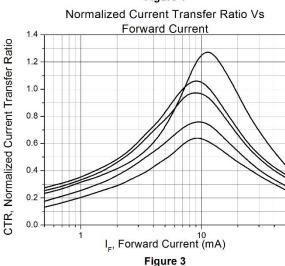
Switching Characteristics

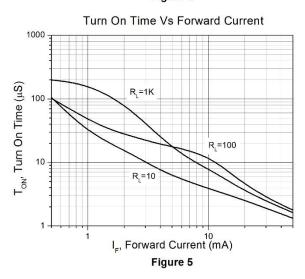
Symbol	Para	ameters	Test Conditions	Min	Тур	Мах	Units	Notes
	Turn On Time	4N2X, 4N3X,	I _F = 200mA, I _c = 50mA, R _L =	-	-	4.7	- µs	
T		TIL113	100Ω					
T _{ON}		LI11DV	I _F = 10mA, V _{CE} = 10V, R _L =		24			
		H11BX 100Ω -	-	24	-			
	Turn Off Time	4N29, 4N30,				20		
		4N31	I _F = 200mA, I _c = 50mA, R _L =	-	-	30		
T		4N32, 4N33,	100Ω			00]	
Toff		TIL113		-	-	90	μs	
		H11BX	I _F = 10mA, V _{CE} = 10V, R _L =		17	17 -		
		ППВА	100Ω	-	''			

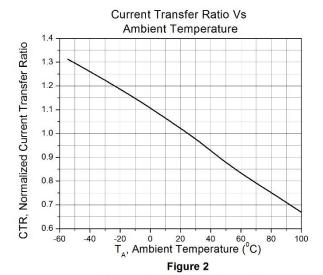


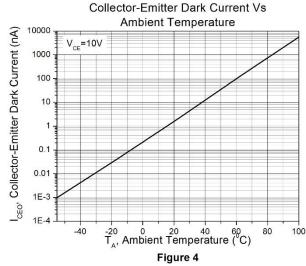
Typical Characteristic Curves

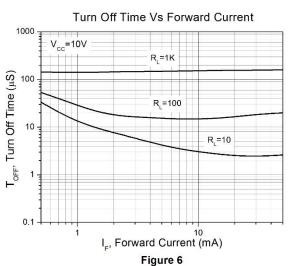








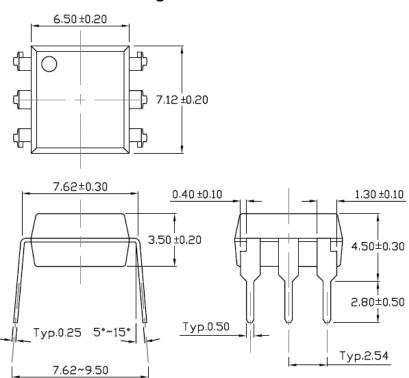




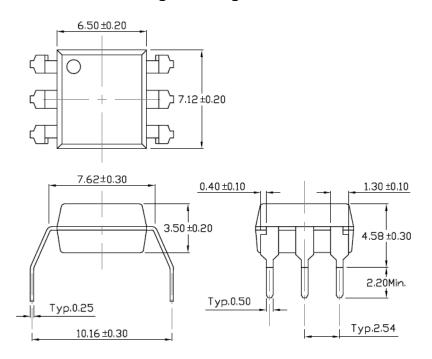


Package Dimension Dimensions in mm unless otherwise stated

Standard DIP - Through Hole

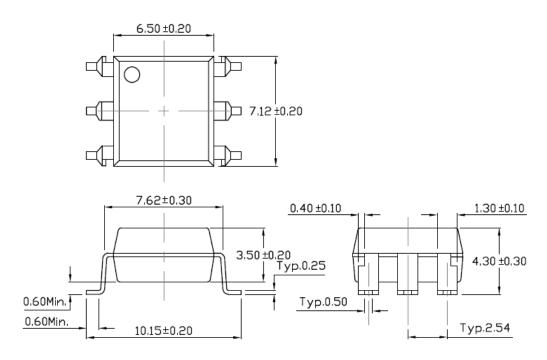


Wide Lead Forming - Through Hole

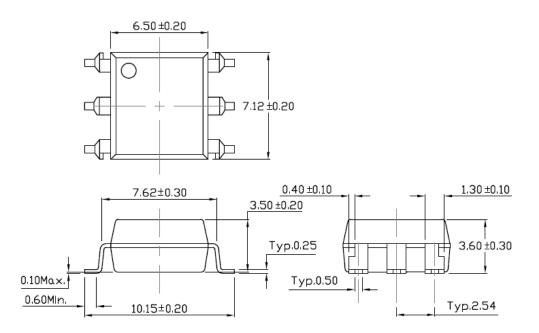




Surface Mount Forming

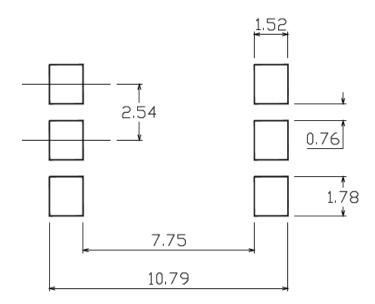


Surface Mount Forming (Low Profile)

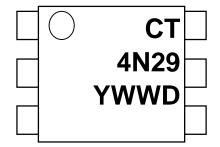




Recommended Solder Mask Dimensions in mm unless otherwise stated



Marking Information



Note:

CT: Logo

4N29 : Product Number

Y : Fiscal Year WW : Work Week

D : Production Code



Ordering Information

4N2X(Y)(Z)-G, 4N3X(Y)(Z)-G, H11BX(Y)(Z)-G

X = Part. No. (9 for 4N2X), (0,1,2,3 for 4N3X series), (1,2,3,255 for H11BX series)

Y = Lead form option (S, SL, M or none)

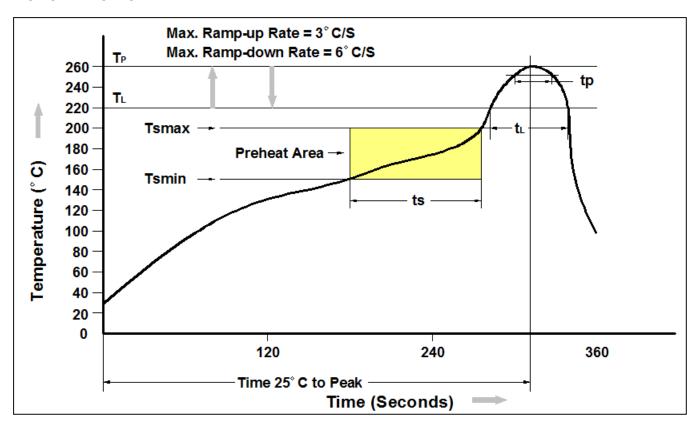
Z = Tape and reel option (TA, TB or none)

G= Material option (G: Green, None: Non-green)

Option	Description	Quantity	
None	None Standard 6 Pin Dip		
М	M Wide Lead Forming		
S(TA)	S(TA) Surface Mount Lead Forming – With Option A Taping		
S(TB)	S(TB) Surface Mount Lead Forming – With Option B Taping		
SL(TA)	SL(TA) Surface Mount Lead Forming(Low Profile) – With Option A Taping		
SL(TB)	1000 Units/Reel		



Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t⊳)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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